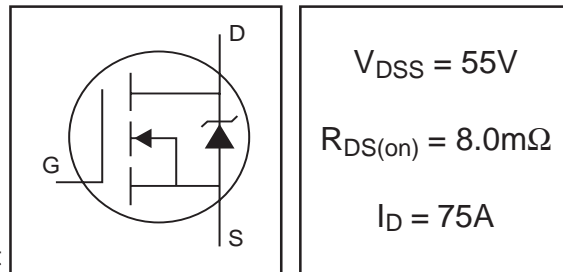


Features

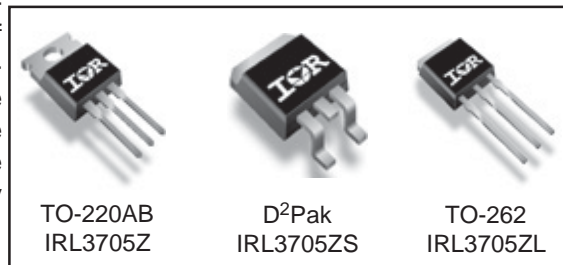
- Logic Level
- Advanced Process Technology
- Ultra Low On-Resistance
- 175°C Operating Temperature
- Fast Switching
- Repetitive Avalanche Allowed up to Tjmax
- Lead-Free

Description

Specifically designed for Automotive applications, this HEXFET® Power MOSFET utilizes the latest processing techniques to achieve extremely low on-resistance per silicon area. Additional features of this design are a 175°C junction operating temperature, fast switching speed and improved repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in Automotive applications and a wide variety of other applications.



$V_{DSS} = 55V$
 $R_{DS(on)} = 8.0m\Omega$
 $I_D = 75A$



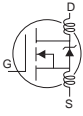
Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$ (Silicon Limited)	86	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	61	
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$ (Package Limited)	75	
I_{DM}	Pulsed Drain Current ①	340	
$P_D @ T_C = 25^\circ C$	Power Dissipation	130	W
	Linear Derating Factor	0.88	W/°C
V_{GS}	Gate-to-Source Voltage	± 16	V
E_{AS} (Thermally limited)	Single Pulse Avalanche Energy ②	120	mJ
E_{AS} (Tested)	Single Pulse Avalanche Energy Tested Value ③	180	
I_{AR}	Avalanche Current ①	See Fig.12a, 12b, 15, 16	A
E_{AR}	Repetitive Avalanche Energy ⑤		mJ
T_J	Operating Junction and	-55 to + 175	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	
	Mounting Torque, 6-32 or M3 screw ⑦	10 lbf•in (1.1N•m)	

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	1.14	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat Greased Surface ⑦	0.50	—	
$R_{\theta JA}$	Junction-to-Ambient ⑦	—	62	
$R_{\theta JA}$	Junction-to-Ambient (PCB Mount) ⑧	—	40	

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	55	—	—	V	V _{GS} = 0V, I _D = 250μA
ΔV _{(BR)DSS} /ΔT _J	Breakdown Voltage Temp. Coefficient	—	0.055	—	V/°C	Reference to 25°C, I _D = 1mA
R _{DS(on)}	Static Drain-to-Source On-Resistance	—	6.5	8.0	mΩ	V _{GS} = 10V, I _D = 52A ③
		—	—	11		V _{GS} = 5.0V, I _D = 43A ③
		—	—	12		V _{GS} = 4.5V, I _D = 30A ③
V _{GS(th)}	Gate Threshold Voltage	1.0	—	3.0	V	V _{DS} = V _{GS} , I _D = 250μA
g _{fs}	Forward Transconductance	150	—	—	V	V _{DS} = 25V, I _D = 52A
I _{DSS}	Drain-to-Source Leakage Current	—	—	20	μA	V _{DS} = 55V, V _{GS} = 0V
		—	—	250		V _{DS} = 55V, V _{GS} = 0V, T _J = 125°C
I _{GSS}	Gate-to-Source Forward Leakage	—	—	200	nA	V _{GS} = 16V
	Gate-to-Source Reverse Leakage	—	—	-200		V _{GS} = -16V
Q _g	Total Gate Charge	—	40	60	nC	I _D = 43A
Q _{gs}	Gate-to-Source Charge	—	12	—		V _{DS} = 44V
Q _{gd}	Gate-to-Drain ("Miller") Charge	—	21	—		V _{GS} = 5.0V ③
t _{d(on)}	Turn-On Delay Time	—	17	—	ns	V _{DD} = 28V
t _r	Rise Time	—	240	—		I _D = 43A
t _{d(off)}	Turn-Off Delay Time	—	26	—		R _G = 4.3 Ω
t _f	Fall Time	—	83	—		V _{GS} = 5.0V ③
L _D	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
L _S	Internal Source Inductance	—	7.5	—		
C _{iss}	Input Capacitance	—	2880	—	pF	V _{GS} = 0V
C _{oss}	Output Capacitance	—	420	—		V _{DS} = 25V
C _{rss}	Reverse Transfer Capacitance	—	220	—		f = 1.0MHz
C _{oss}	Output Capacitance	—	1500	—		V _{GS} = 0V, V _{DS} = 1.0V, f = 1.0MHz
C _{oss}	Output Capacitance	—	330	—		V _{GS} = 0V, V _{DS} = 44V, f = 1.0MHz
C _{oss eff.}	Effective Output Capacitance	—	510	—		V _{GS} = 0V, V _{DS} = 0V to 44V ④

Source-Drain Ratings and Characteristics

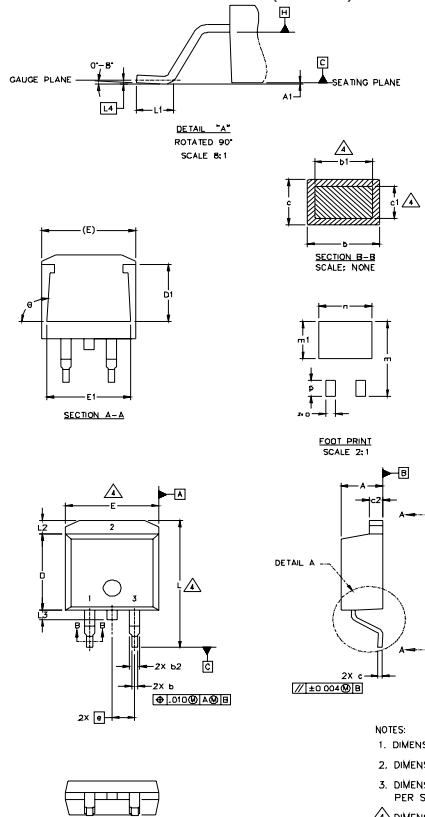
	Parameter	Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)	—	—	75	A	MOSFET symbol showing the integral reverse
I _{SM}	Pulsed Source Current (Body Diode) ①	—	—	340		p-n junction diode.
V _{SD}	Diode Forward Voltage	—	—	1.3	V	T _J = 25°C, I _S = 52A, V _{GS} = 0V ③
t _{rr}	Reverse Recovery Time	—	16	24	ns	T _J = 25°C, I _F = 43A, V _{DD} = 28V
Q _{rr}	Reverse Recovery Charge	—	7.4	11	nC	di/dt = 100A/μs ③
t _{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

IRL3705Z/S/LPbF

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D²Pak Package Outline

Dimensions are shown in millimeters (inches)



SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	
A1		0.127		.005	
b	0.51	0.99	.020	.039	4
b1	0.51	0.89	.020	.035	
b2	1.14	1.40	.045	.055	
c	0.43	0.63	.017	.025	4
c1	0.38	0.74	.015	.029	
c2	1.14	1.40	.045	.055	
D	8.51	9.65	.335	.380	3
D1	5.33		.210		
E	9.65	10.67	.380	.420	3
E1	6.22		.245		
e	2.54 BSC		.100 BSC		
L	14.61	15.88	.575	.625	
L1	1.78	2.79	.070	.110	
L2		1.65		.065	
L3	1.27	1.78	.050	.070	
L4	0.25 BSC		.010 BSC		
m	17.78		.700		
m1	8.89		.350		
n	11.43		.450		
o	2.08		.082		
p	3.81		.150		
θ	90°	93°	90°	93°	

LEAD ASSIGNMENTS

HEXFET	IGBTs, CoPACK	DIODES
1 - GATE	1 - GATE	1 - ANODE *
2 - DRAIN	2 - COLLECTOR	2 - CATHODE
3 - SOURCE	3 - EMITTER	3 - ANODE

* PART DEPENDENT.

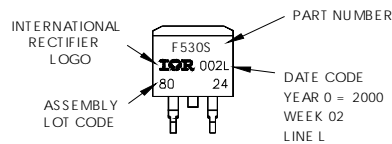
NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [0.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
4. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
5. CONTROLLING DIMENSION: INCH.

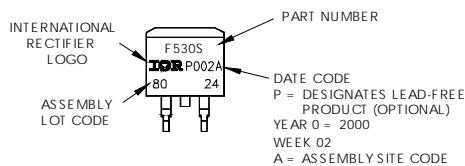
D²Pak Part Marking Information

EXAMPLE: THIS IS AN IRF530S WITH
LOT CODE 8024
ASSEMBLED ON WW 02, 2000
IN THE ASSEMBLY LINE "L"

Note: "P" in assembly line
position indicates "Lead-Free"



OR

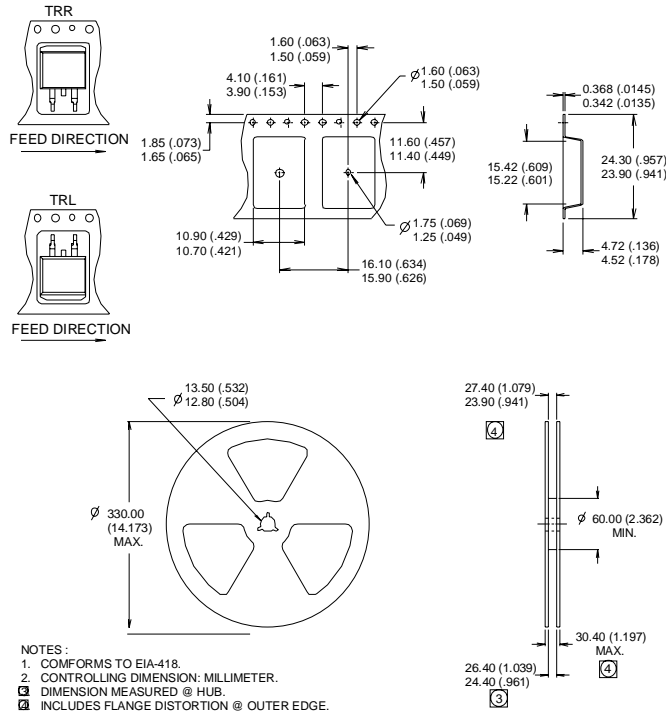


IRL3705Z/S/LPbF

D²Pak Tape & Reel Information

Dimensions are shown in millimeters (inches)

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NOTES:
 1. CONFORMS TO EIA-418.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSION MEASURED @ HUB.
 4. INCLUDES FLANGE DISTORTION @ OUTER EDGE.

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11).
- ② Limited by T_{Jmax} , starting $T_J = 25^\circ C$, $L = 0.09mH$, $R_G = 25\Omega$, $I_{AS} = 52A$, $V_{GS} = 10V$. Part not recommended for use above this value.
- ③ Pulse width $\leq 1.0ms$; duty cycle $\leq 2\%$.
- ④ C_{OSS} eff. is a fixed capacitance that gives the same charging time as C_{OSS} while V_{DS} is rising from 0 to 80% V_{DSS} .
- ⑤ Limited by T_{Jmax} , see Fig.12a, 12b, 15, 16 for typical repetitive avalanche performance.
- ⑥ This value determined from sample failure population. 100% tested to this value in production.
- ⑦ This is only applied to TO-220AB package.
- ⑧ This is applied to D²Pak, when mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994.
- ⑨ R_θ is measured at T_J of approximately $90^\circ C$.

TO-220AB package is not recommended for Surface Mount Application.

Data and specifications subject to change without notice.
 This product has been designed and qualified for the Automotive [Q101]market.

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